

Supplementary Information for

**Emergence of a bismuth-based metal–organic framework as an X-ray scintillator**

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## Experimental Procedures

### Materials and synthesis

**Materials.**  $\text{Bi}(\text{NO}_3)_3 \cdot 5\text{H}_2\text{O}$  (99.9%, Shanghai Aladdin Biochemical Technology Co., Ltd.), 1,1,2,2-tetra(4-carboxylphenyl)ethylene ( $\text{H}_4\text{TCPE}$ ) (95%, Shanghai Adamas Reagent Co., Ltd.),  $\text{HNO}_3$  (GR, 96%, Sinopharm Chemical Reagent Co., Ltd.), and dimethylformamide (99.5%, Shanghai Macklin Biochemical Co., Ltd) were used as received from commercial suppliers without further purification.

**Synthesis. Bi-TCPE.** A mixture of  $\text{Bi}(\text{NO}_3)_3 \cdot 5\text{H}_2\text{O}$  (0.001 mmol),  $\text{H}_4\text{TCPE}$  (0.001 mmol),  $\text{HNO}_3$  (45  $\mu\text{L}$ ), and DMF (1000  $\mu\text{L}$ ) was loaded into a 7 mL glass vial. The vial was sealed and heated at 100 °C for 48 h, then cooled to room temperature under ambient conditions. Yellow, tablet-shaped single crystals of **Bi-TCPE** were obtained, washed with ethanol, and dried under ambient conditions.

### Characterizations

Single-crystal X-ray diffraction (SCXRD) analysis was performed on a Bruker D8-Venture single-crystal X-ray diffractometer equipped with an I $\mu$ S 3.0 microfocus X-ray source (Mo  $\text{K}\alpha$  radiation,  $\lambda = 0.71073 \text{ \AA}$ ) and a CMOS detector at 298 K. Data collection and reduction were carried out using the APEX3 program. The crystal structure was solved by intrinsic phasing using ShelXT and refined by full-matrix least-squares techniques with ShelXL, as interpreted by the Olex2 software.

Powder X-ray diffraction (PXRD) patterns were collected on a Bruker D8 Advance diffractometer (40 kV, 40 mA) with Cu  $\text{K}\alpha$  radiation ( $\lambda = 1.54060 \text{ \AA}$ ) at a step size of 0.02°. The simulated PXRD pattern of **Bi-TCPE** was generated from its crystallographic information file (CIF) using Materials Studio.

Photoluminescence (PL) spectra, time-resolved PL lifetimes, and photoluminescence quantum yields (PLQYs) were measured at room temperature using an Edinburgh FLS980 fluorescence spectrometer.

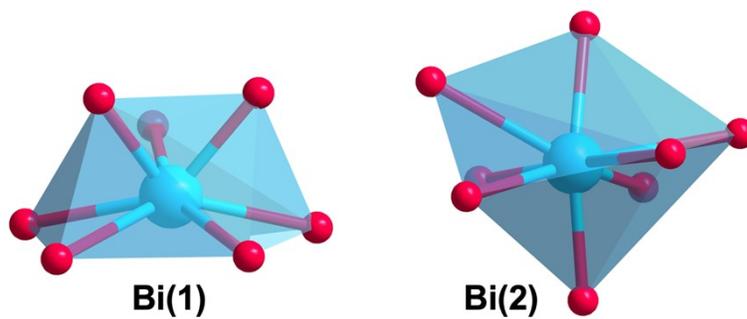
X-ray-induced radioluminescence (RL) spectra were obtained under a tungsten (W)  $\text{K}\alpha$  radiation source (70 kV, 12 W), and the emission was recorded using a NOVA cooled fiber optic spectrometer.

Thermogravimetric analysis (TGA) was conducted using a Waters SDT650 simultaneous thermal analyzer under a dry nitrogen atmosphere from 30 to 800 °C at a heating rate of 10 °C/min.

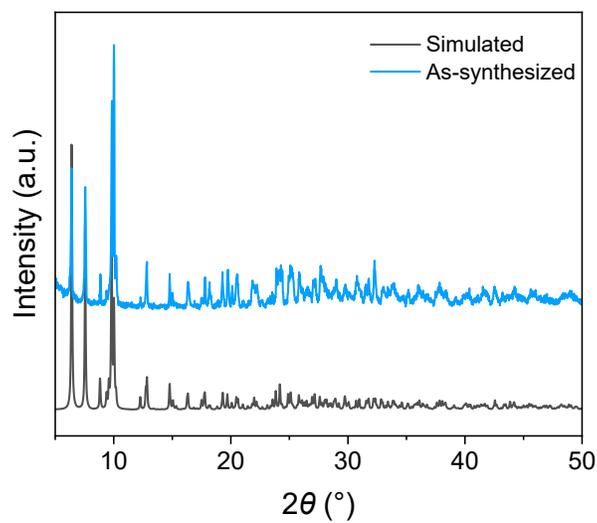
Fourier-transform infrared (FTIR) spectra were recorded on a Nicolet iS50 FTIR spectrometer in the range of 640–4000  $\text{cm}^{-1}$ .

### Fabrication of flexible Bi-TCPE/ PDMS scintillator film

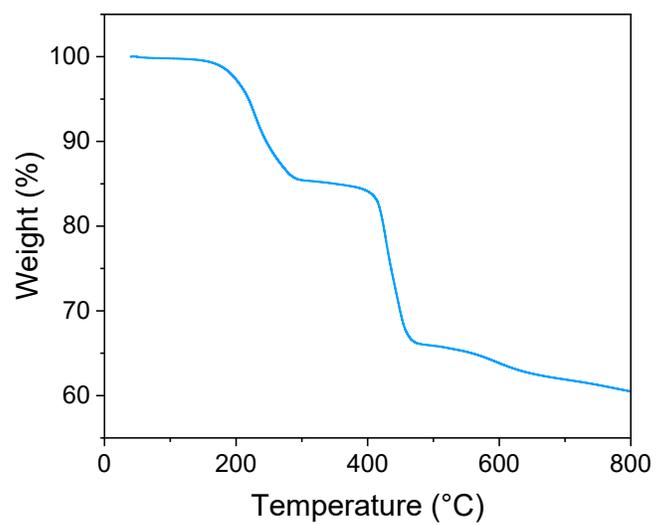
A 10:1 weight ratio of polydimethylsiloxane (PDMS) base to curing agent (SYLGARD 184) was thoroughly mixed. Subsequently, **Bi-TCPE** powder (20 wt%) was incorporated and uniformly dispersed through vigorous stirring. The homogenous mixture was then cast onto a flat glass surface, leveled using a blade, and thermally cured at 100 °C for 1 h to produce the **Bi-TCPE/ PDMS** scintillator film.



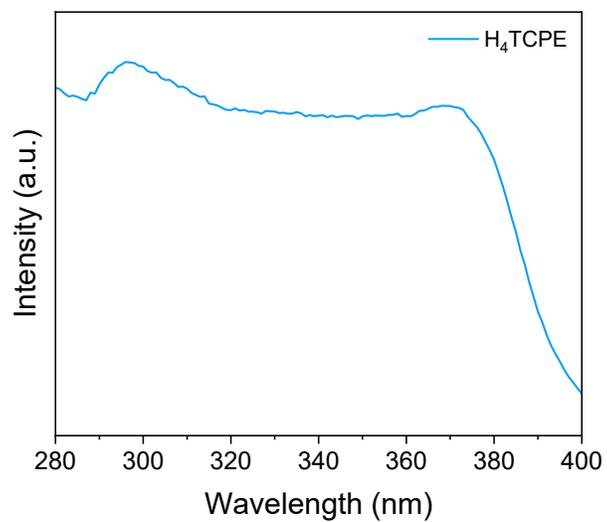
**Fig. S1** Coordination environments of Bi(1) and Bi(2) in **Bi-TCPE**.



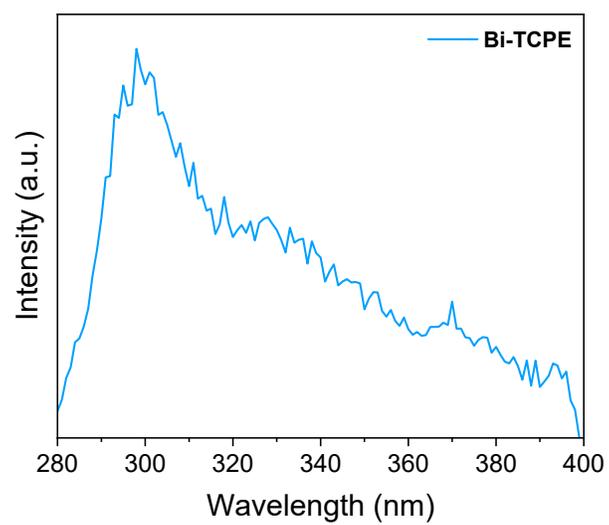
**Fig. S2** Simulated and as-synthesized PXRD patterns of **Bi-TCPE**.



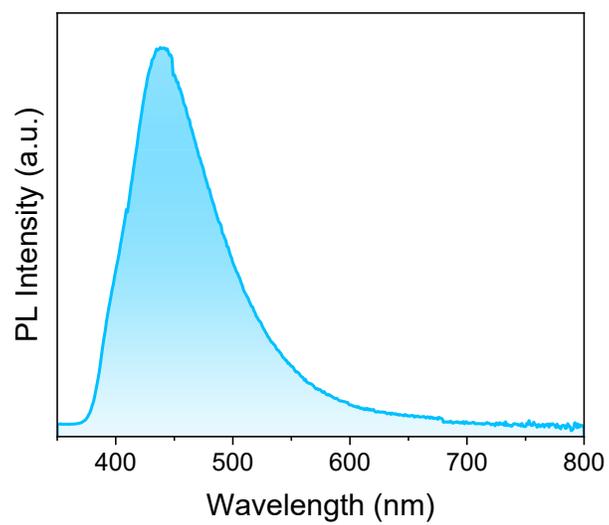
**Fig. S3** Thermogravimetric analysis (TGA) curve of **Bi-TCPE**.



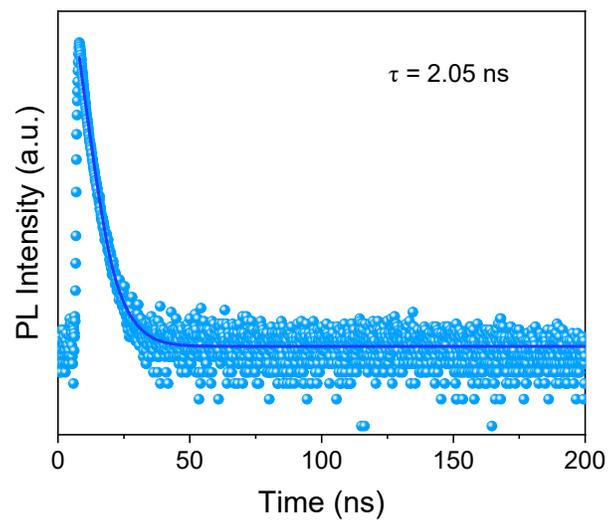
**Fig. S4** Excitation spectrum of H<sub>4</sub>TCPE.



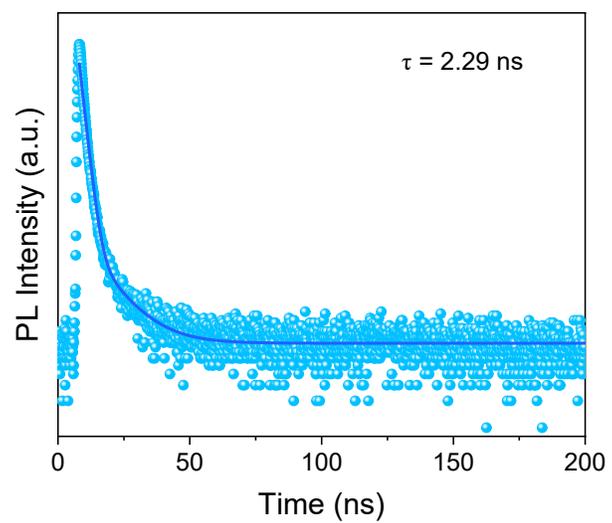
**Fig. S5** Excitation spectrum of **Bi-TCPE**.



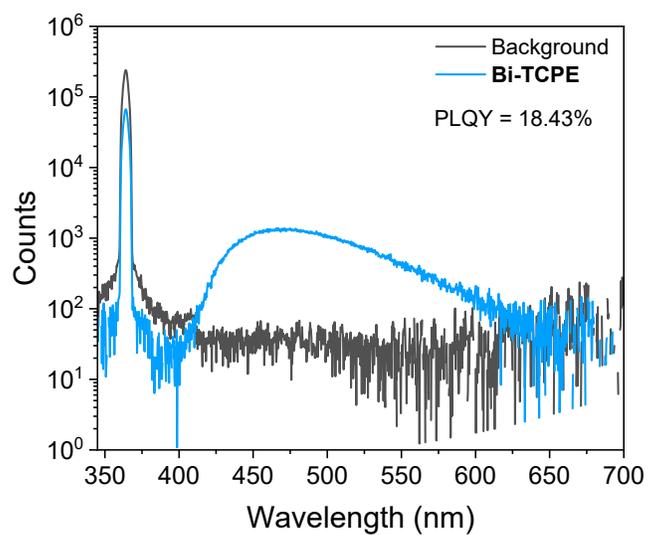
**Fig. S6** Photoluminescence spectrum of H<sub>4</sub>TCPE.



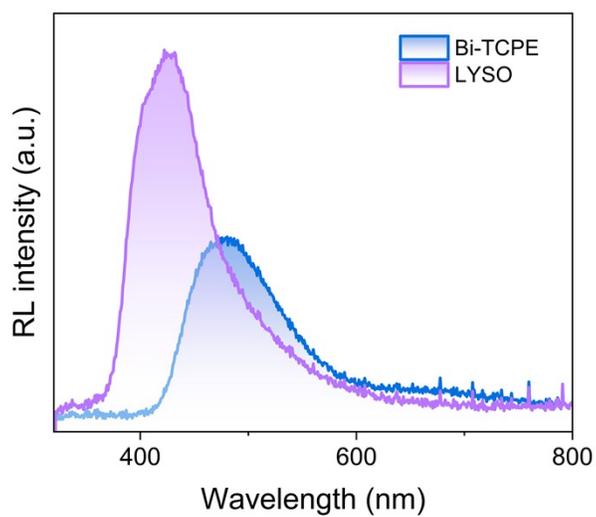
**Fig. S7** Time-resolved photoluminescence decay profile of **Bi-TCPE**.



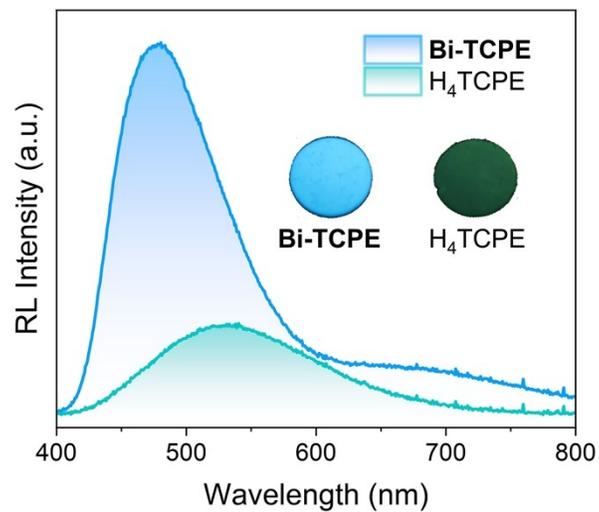
**Fig. S8** Time-resolved photoluminescence decay profile of H<sub>4</sub>TCPE.



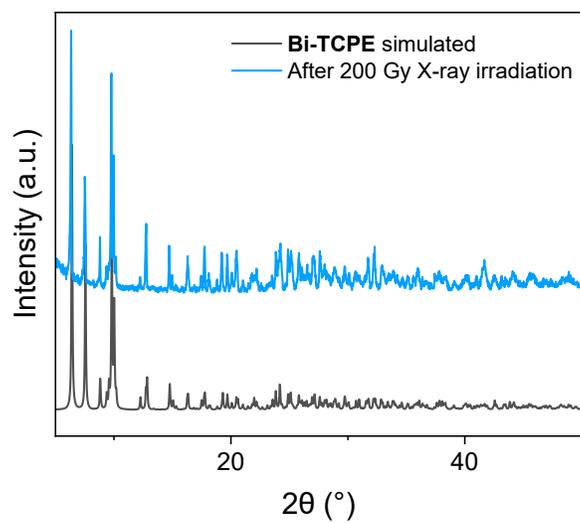
**Fig. S9** Photoluminescence quantum yield of **Bi-TCPE**.



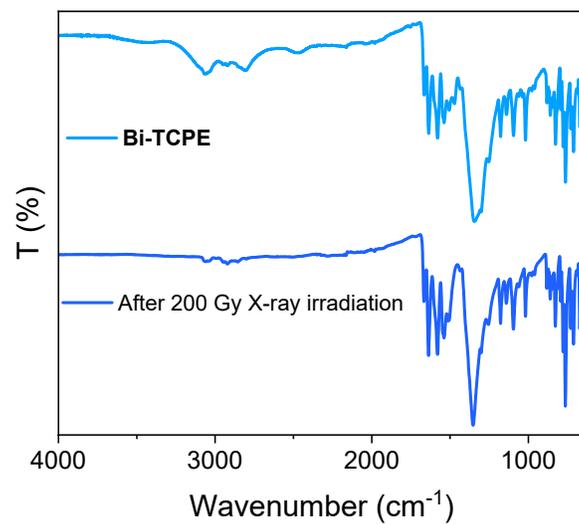
**Fig. S10** Radioluminescence spectra of **Bi-TCPE** and **LYSO** under comparable irradiation condition.



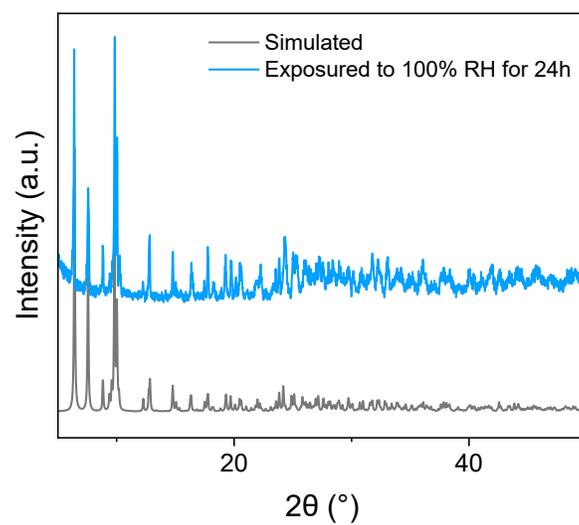
**Fig. S11** Radioluminescence spectra and photographs of **Bi-TCPE** and **H<sub>4</sub>TCPE** under comparable irradiation condition.



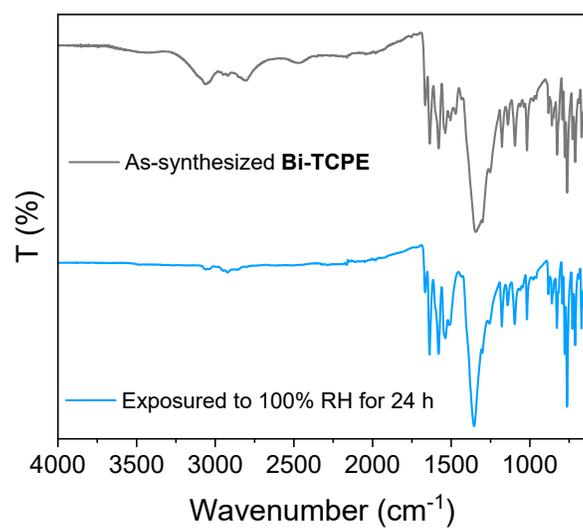
**Fig. S12** PXRD patterns of **Bi-TCPE** before and after X-ray irradiation.



**Fig. S13** FTIR spectra of **Bi-TCPE** before and after X-ray irradiation.



**Fig. S14** PXRD patterns of **Bi-TCPE** before and after exposure to 100% relative humidity (RH).



**Fig. S15** FTIR spectra of **Bi-TCPE** before and after exposure to 100% relative humidity (RH).

**Table S1** Crystallographic data for **Bi-TCPE**.

Compound	Bi-TCPE
CCDC	2443648
Formula	C <sub>33</sub> H <sub>23</sub> O <sub>10</sub> Bi <sub>2</sub>
Formula weight	1011.48
$\rho_{calc}$ (g cm <sup>-3</sup> )	1.891
$\mu$ (mm <sup>-1</sup> )	7.424
Colour	Yellow
Habit	block
Space group	<i>P</i> -1
<i>a</i> (Å)	11.032(4)
<i>b</i> (Å)	12.390(4)
<i>c</i> (Å)	14.370(4)
$\alpha$ (deg)	85.718(10)
$\beta$ (deg)	73.575(10)
$\gamma$ (deg)	70.606(12)
<i>V</i> (Å <sup>3</sup> )	1776.7(10)
<i>Z</i>	2
<i>T</i> (K)	293.00
$\lambda$ (Å)	0.711
$\Theta_{max}$ (deg)	25.027
<i>R</i> <sub>1</sub>	0.0418
$\omega R$ <sub>2</sub>	0.1080
<i>R</i> <sub>int</sub>	0.0698
<i>Goof</i>	1.013

**Table S2** Selected bond distances and bond valence sums of Bi(1) and Bi(2) in **Bi-TCPE**.

	Bond Distance (Å)	Bond Distance (Å)	
Bi(1)-O(1)	2.167	Bi2-O1	2.146
Bi(1)-O(1)#1	2.209	Bi2-O8	2.268
Bi(1)-O(3)	2.260	Bi2-O6	2.332
Bi(1)-O(7)	2.540	Bi2-O4	2.472
Bi(1)-O(2)	2.542	Bi2-O9	2.492
Bi(1)-O(10)	2.609	Bi2-O10	2.798
Bi(1)-O(6)	2.762	Bi2-O5	2.886
		Bi2-O5	2.887
Bi(1) BVS	3.167	Bi(2) BVS	3.071